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MUR805 THRU MUR840

Features

- Glass passivated chip
- Superfast switching time for high efficiency
- Low reverse leakage current
- High surge capacity

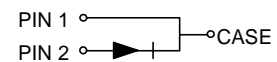
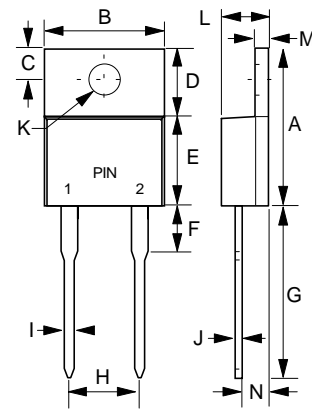
Maximum Ratings

- Operating Junction Temperature: -55°C to +150°C
- Storage Temperature: -55°C to +150°C

8 Amp Super Fast Glass Passivated Rectifier 50 to 400 Volts

Catalog Number	Device Marking	Maximum Recurrent Peak Reverse Voltage	Maximum RMS Voltage	Maximum DC Blocking Voltage
MUR805	MUR805	50V	35V	50V
MUR810	MUR810	100V	70V	100V
MUR820	MUR820	200V	140V	200V
MUR840	MUR840	400V	320V	400V

TO-220AC



Electrical Characteristics @ 25°C Unless Otherwise Specified

Average Forward Current	$I_{F(AV)}$	8.0A	$T_C = 100^\circ\text{C}$
Peak Forward Surge Current	I_{FSM}	125A	8.3 ms, half sine
Maximum Forward Voltage Drop Per Element MUR805 ~MUR820 MUR840	V_F	1.0V 1.3V	$I_{FM} = 8\text{ A}$ $T_J = 25^\circ\text{C}$
Maximum DC Reverse Current At Rated DC Blocking Voltage	I_R	10 uA 500uA	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$
Maximum Reverse Recovery Time	T_{rr}	50ns	$I_F=0.5\text{A}, I_R=1.0\text{A},$ $I_{rr}=0.25\text{A}$

DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.560	.625	14.22	15.88	
B	.380	.420	9.65	10.67	
C	.100	.135	2.54	3.43	
D	.230	.270	5.84	6.86	
E	.380	.420	9.65	10.67	
F	-----	.250	-----	6.35	
G	.500	.580	12.70	14.73	
H	.190	.210	4.83	5.33	
I	.020	.045	0.51	1.14	
J	.012	.025	0.30	0.64	
K	.139	.161	3.53	4.09	∅
L	.140	.190	3.56	4.83	
M	.045	.055	1.14	1.40	
N	.080	.115	2.03	2.92	

*Pulse test: Pulse width 300 μsec, Duty cycle 2%

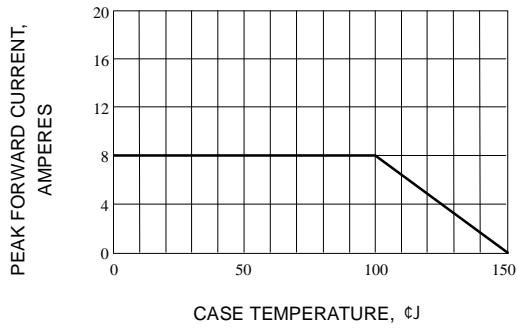


Fig. 1-TYPICAL FORWARD CURRENT DERATING CURVE

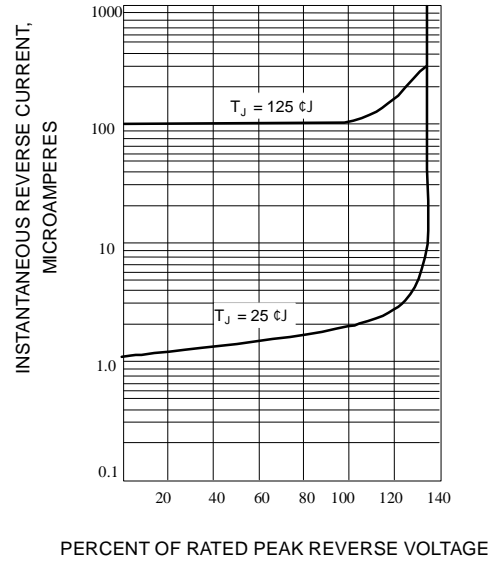


Fig. 2-TYPICAL REVERSE CHARACTERISTICS

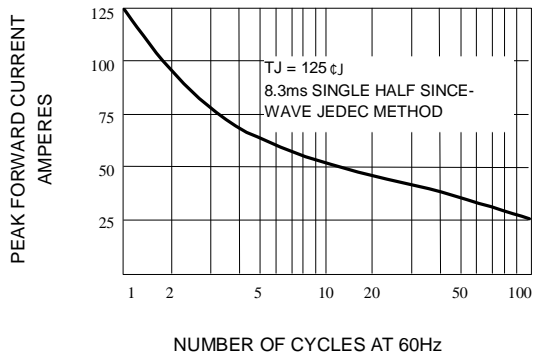


Fig. 3-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

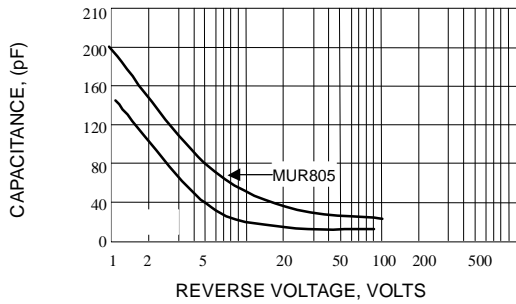


Fig. 4-TYPICAL JUNCTION CAPACITANCE

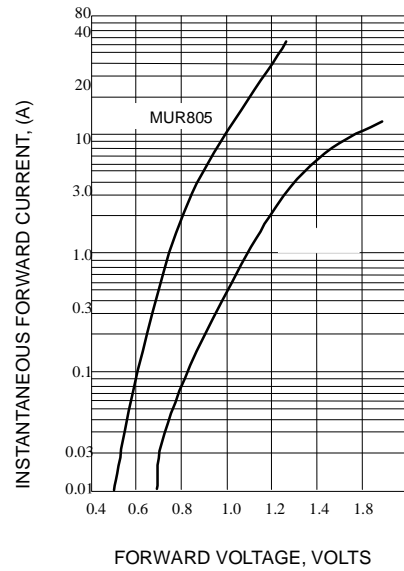


Fig. 5-TYPICAL FORWARD CURRENT